

L Number	Hits	Search Text	DB	Time stamp
1	211	shibata near2 kazutaka.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/10 10:28
2	137	(shibata near2 kazutaka.in.) and resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/10 10:28
3	17	((shibata near2 kazutaka.in.) and resin) and (polish\$4 or grind\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/10 10:30
4	6	((shibata near2 kazutaka.in.) and resin) and (polish\$4 or grind\$5)) and chip\$lon\$lchip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/10 10:30
-	1569	resin same (polish\$ or grind\$) same (rear or back or back\$lside)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 16:49
-	755	resin same (polish\$ or grind\$) near10 (rear or back or back\$lside)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 16:49
-	318	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$lside)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 16:49
-	50	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$lside) same electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 16:56
-	172	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$lside) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 17:53
-	70	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$lside) same chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 17:28
-	5	ichikawa.in. near2 kimiya and resin same semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 17:22
-	46	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$lside) near20 expos\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 17:53
-	172	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$lside) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 17:53
-	131	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$lside) and chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/18 18:12

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-	34	(resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) and chip) not ((resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) same electrode) or (resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) same chip) or (resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) near20 expos\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 10:17
-	192	resin near10 (polish\$4 or grind\$) near10 thick\$ and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 10:18
-	44	resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 11:26
-	262	resin near10 (polish\$4 or grind\$) same (back or back\$1side or rear) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 10:40
-	172	resin near10 (polish\$4 or grind\$) near10 (back or back\$1side or rear) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 10:40
-	133	(resin near10 (polish\$4 or grind\$) near10 (back or back\$1side or rear) and semiconductor) not (resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 10:41
-	7	resin near10 (polish\$4 or grind\$) near10 thick\$ same bottom and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 11:28
-	54	resin near10 (polish\$4 or grind\$) near10 bottom and semiconductor not (resin near10 (polish\$4 or grind\$) near10 thick\$ same bottom and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 11:49
-	2	02153527.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 11:50
-	1216	etch\$ same (grind\$ or polish\$) same resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 13:02
-	150	etch\$ near10 (grind\$ or polish\$) near10 resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 13:03
-	94	etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 13:05
-	38	(etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/19 13:06

-	2	6495914.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 11:18
-	0	chip adj on adj chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 11:18
-	488	chip\$lon\$lchip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 11:19
-	240	chip\$lon\$lchip near5 structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 11:20
-	32	chip\$lon\$lchip near5 structure same electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 11:25
-	54	chip\$lon\$lchip same resin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 11:44
-	25	chip\$lon\$lchip near10 advantag\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 11:59
-	2	5977640.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 11:59